# RQ3G120BJFRA

Pch -40V -12A Power MOSFET

Datasheet

$V_{DSS}$	-40V
R <sub>DS(on)</sub> (Max.)	48mΩ
I <sub>D</sub>	±12A
P <sub>D</sub>	40W

# <del>-</del>

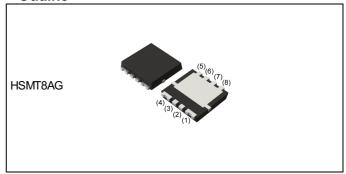
Features

- 1) Small high-powered package reduces mounting area by 64% at a maximum
- 2) Realization of high mounting reliability by original terminal and plating treatment
- 3) AEC-Q101 Qualified

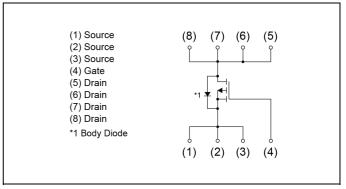
### Application

ADAS/Info./Lighting/Body

### Outline



### Inner circuit



Packaging specifications

or ackaging specifications							
	Packing	Embossed Tape					
	Reel size (mm)	330					
Туре	Tape width (mm)	12					
	Quantity (pcs)	3000					
	Taping code	TCB					
	Marking	G120BJ					

### ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		V <sub>DSS</sub>	-40	V
Continuous drain current	V <sub>GS</sub> = -10V	I <sub>D</sub> *1	±12	А
Pulsed drain current		I <sub>DP</sub> *2	±24	Α
Gate - Source voltage		$V_{GSS}$	+5/-20	V
Avalanche current, single pulse		I <sub>AS</sub> *3	11	Α
Avalanche energy, single pulse		E <sub>AS</sub> *3	9	mJ
Power dissipation		P <sub>D</sub> *1	40	W
Junction temperature		T <sub>j</sub>	150	°C
Operating junction and storage temper	rature range	T <sub>stg</sub>	-55 to +150	°C

### ●Thermal resistance

Parameter	Symbol	Values			Lloit
		Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub> *1	-	ı	3.1	°C/W

### ● Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	OI CONDITIONS		Тур.	Max.	Offic
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{(BR)DSS}$ $V_{GS} = 0V, I_D = -1mA$		-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	$\frac{\Delta V_{(BR)DSS}}{\Delta T_i} I_D = -1 \text{mA}$ referenced to 25°C		-22	-	mV/°C
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = -32V, V_{GS} = 0V$	-	-	-1	μA
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = +5/-20V, V_{DS} = 0V$	1	-	±500	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -279 \mu A$	-1.0	-	-2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta  V_{GS(th)}}{\Delta  T_j}$	$I_D = -279\mu A$ referenced to 25°C	-	3.1	-	mV/°C
Static drain - source	D *4	V <sub>GS</sub> = -10V, I <sub>D</sub> = -12A	-	38	48	mΩ
on - state resistance	R <sub>DS(on)</sub> *4	$V_{GS} = -4.5V, I_D = -6A$	-	47	60	11122
Gate resistance	$R_G$	f = 1MHz, open drain	-	15	-	Ω
Forward Transfer Admittance	Y <sub>fs</sub>  *4	V <sub>DS</sub> = -5V, I <sub>D</sub> = -10A	6.5	-	-	S

<sup>\*1</sup>  $T_c$ =25°C , Limited only by maximum junction temperature  $T_i$ =150°C.

<sup>\*2</sup> Pw ≤10µs , Duty cycle ≤1%

<sup>\*3</sup> L=0.1mH,  $V_{DD}$ =-20V,  $R_G$ =25 $\Omega$ , Starting  $T_i$ =25 $^{\circ}$ C, See Fig.3-1,3-2

<sup>\*4</sup> Pulsed

### ● Electrical characteristics (T<sub>a</sub> = 25°C)

Darameter	Cumbal	Conditions	Values			Lloit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	750	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -20V	-	95	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	75	-	
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq -20V, V_{GS} = -10V$	1	6.7	1	
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = -10A	1	4.7	ı	no
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L \simeq 2\Omega$		36		ns
Fall time	t <sub>f</sub> *4	$R_G = 1\Omega$	-	9.8	-	

### ● Gate charge characteristics (T<sub>a</sub> = 25°C)

	\ a	,						
Parameter	Symbol	Conditi	0 1111		Values		Unit	
Parameter	Symbol	Conditions		Min.	Тур.	Max.	Offic	
Total gate charge	0	V <sub>DD</sub> ≃ -20V	V <sub>GS</sub> = -10V	-	15.5	-		
Total gate charge	$Q_{g}$			-	7.8	-	C	
Gate - Source charge	$Q_{gs}$		$I_{D} = -10A$	V <sub>GS</sub> = -4.5V	-	2.4	-	nC
Gate - Drain charge	$Q_{gd}$			-	3.1	-		

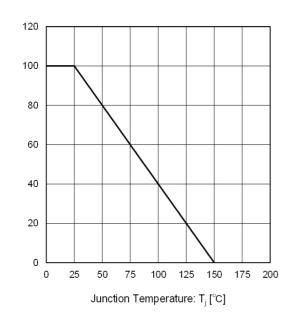
### ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol Conditions		Values			Unit	
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Continuous forward current	I <sub>S</sub>	T = 25°C	-	-	-12	Α	
Pulse forward current	I <sub>SP</sub> *2	$T_a = 25^{\circ}C$	-	-	-24	Α	
Forward voltage	$V_{SD}$	V <sub>GS</sub> = 0V, I <sub>S</sub> = -12A	-	-	-1.2	V	
Reverse recovery time	t <sub>rr</sub>	I <sub>S</sub> = -10A, V <sub>GS</sub> =0V	-	21	-	ns	
Reverse recovery charge	$Q_{rr}$	di/dt = 100A/µs	-	12	-	nC	

Power Dissipation: P<sub>D</sub>/P<sub>Dmax</sub>.

### • Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve



Drain Current : -I<sub>D</sub> [A]

Fig.2 Maximum Safe Operating Area

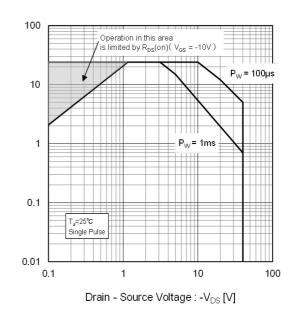


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

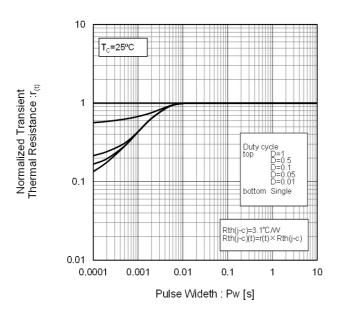
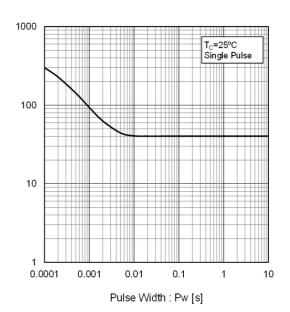


Fig.4 Single Pulse Maximum Power dissipation

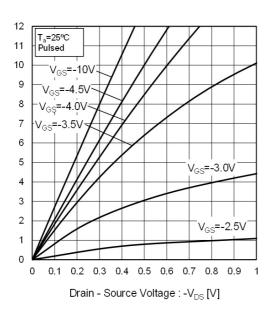


Peak Transient Power: P[W]

Drain Current : -I<sub>D</sub> [A]

### • Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



Drain Current : -I<sub>D</sub> [A]

Fig.6 Typical Output Characteristics(II)

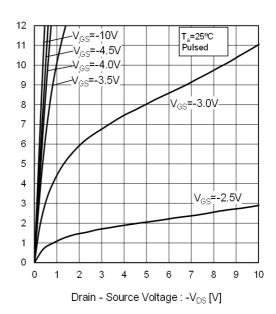


Fig.7 Breakdown Voltage vs.
Junction Temperature

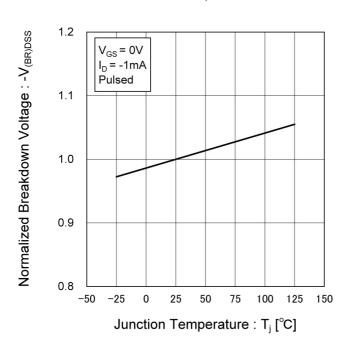


Fig.8 Typical Transfer Characteristics

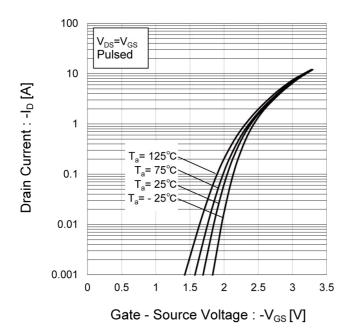


Fig.9 Gate Threshold Voltage vs.
Junction Temperature

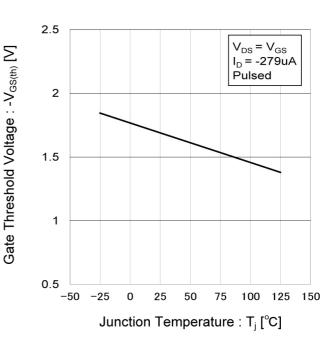


Fig.10 Forward Transfer Admittance vs.
Drain Current

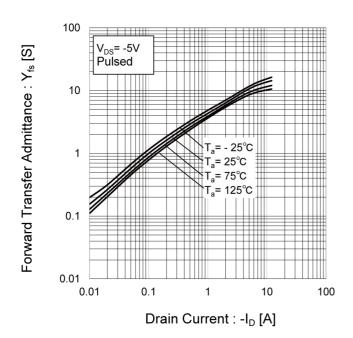


Fig.11 Drain Current Derating Curve

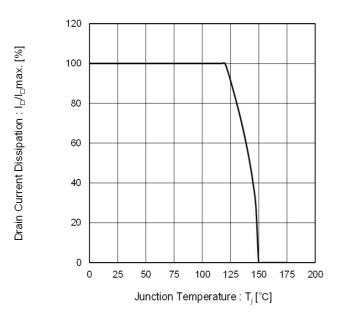
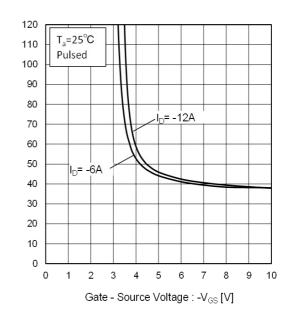


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Static Drain - Source On-State Resistance :  $R_{\mathrm{DS}(\omega)}\left[m\Omega\right]$ 

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

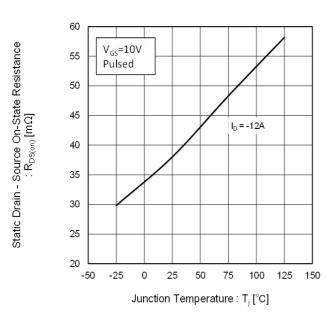


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I)

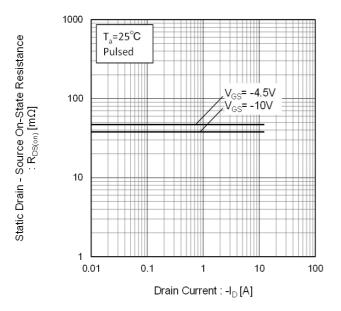


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

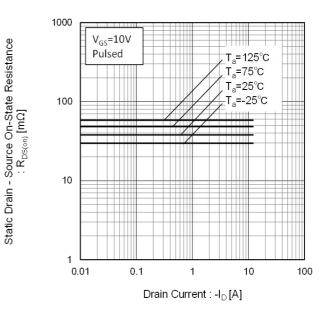


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)

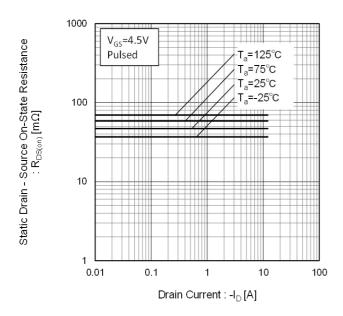


Fig.17 Typical Capacitance vs.

Drain - Source Voltage

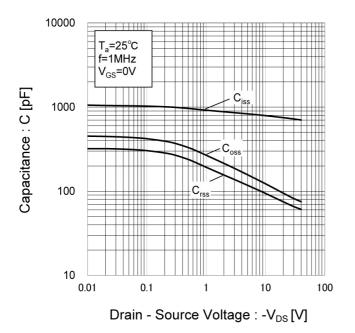


Fig.18 Switching Characteristics

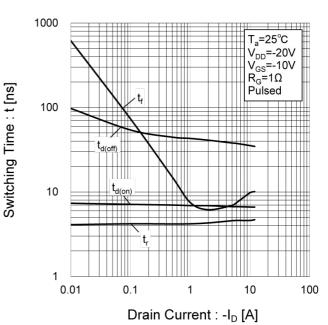


Fig.19 Dynamic Input Characteristics

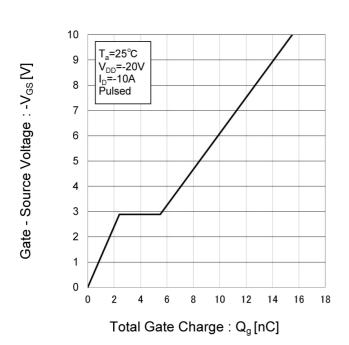
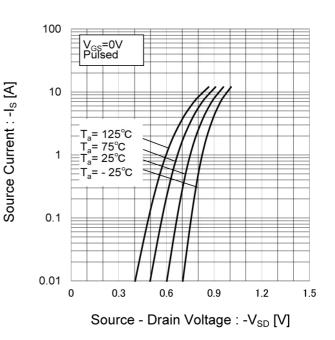


Fig.20 Source Current vs.

Source Drain Voltage



### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

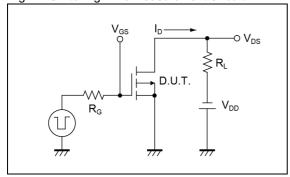


Fig.2-1 Gate Charge Measurement Circuit

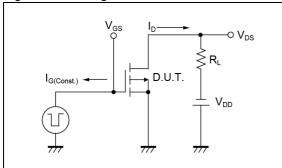


Fig.3-1 Avalanche Measurement Circuit

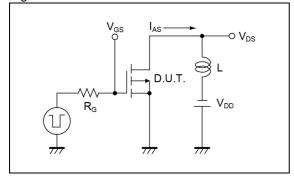


Fig.1-2 Switching Waveforms

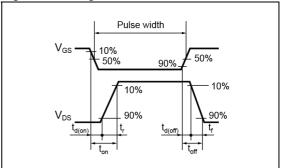


Fig.2-2 Gate Charge Waveform

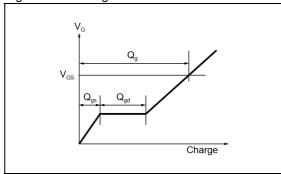
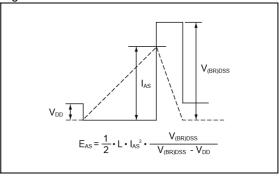
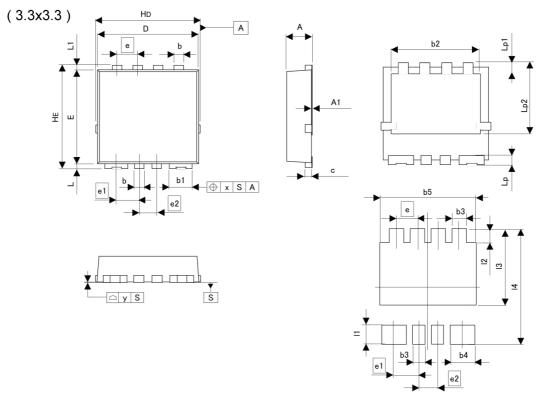


Fig.3-2 Avalanche Waveform



### Dimensions

### HSMT8AG



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIME	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	0.70	0.90	0.028	0.035	
A1	0.00	0.05	0.000	0.002	
b	0.27	0.37	0.011	0.015	
b1	0.69	0.79	0.027	0.031	
b2	2.50	2.70	0.098	0.106	
С	0.10	0.30	0.004	0.012	
D	3.10	3.30	0.122	0.130	
E	2.90	3.10	0.114	0.122	
е	0.	65	0.0	26	
e1	0.	78	0.0	)31	
e2	0.	0.57		)22	
HD	3.20	3.40	0.126	0.134	
HE	3.20	3.40	0.126	0.134	
L	0.07	0.25	0.003	0.010	
L1	0.07	0.25	0.003	0.010	
Lp	0.20	0.40	0.008	0.016	
Lp1	0.25	0.45	0.010	0.018	
Lp2	2.10	2.50	0.083	0.098	
х	1	0.10	-	0.004	
у	-	0.10	-	0.004	

DIM	MILIME	MILIMETERS		HES
DIIVI	MIN	MAX	MIN	MAX
b3	-	0.47	-	0.019
b4		0.89	-	0.035
b5	-	2.70	-	0.106
l1	-	0.50	-	0.020
12	14	0.55	-	0.022
13	-	2.40	-	0.094
14	-	3.40	-	0.134

Dimension in mm/inches



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ſ	JÁPAN	USA	EU	CHINA
Ī	CLASSⅢ	CL ACCIII	CLASS II b	СГУССШ
ſ	CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

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- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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